

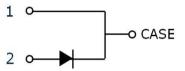
CoolSiC™ Automotive Schottky Diode 650V G5

650V/16A Silicon Carbide Schottky Diode in D2PAK (Real 2 Pins)

Features

- Revolutionary semiconductor material Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Junction Temperature range from -40°C to 175°C
- System efficiency improvement over Si diodes
- System cost/size savings due to reduced cooling requirements
- Enabling higher frequency/increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI





Potential Applications

- Booster/DCDC Converter
- On board Charger/PFC









Product Validation

"Qualified for Automotive Applications. Product Validation according to AEC-Q100/101"

Description

The 5th Generation CoolSiC™ Automotive Schottky Diode represents Infineon leading edge technology for Silicon Carbide Schottky Barrier diodes. Thanks to a compact design and a technology based on thin wafers, this family of products shows improved efficiency over all load conditions resulting from both its thermal characteristics and low figure of merit (Qc x Vf). This product family has been designed to complement Infineon's IGBT and CoolMOS™ portfolio. This ensures meeting the most stringent application requirements in the 650V voltage class.

Product Information				
Ordering Code	AIDK16S65C5			
Marking	AD1665C5			
Package	PG-TO263-2-1			
SP Number	SP001725240			

Parameter	Value/Unit				
$V_{DC,max}$	650 V				
I _F ; T _C < 124 °C	16 A				
$Q_{\rm C}; V_{\rm R} = 400 \rm V$	23 nC				
$E_{\rm C}$; $V_{\rm R}$ = 400 V	5.3 μJ				
$T_{j,max}$	175 ℃				

Pin	Definition
Pin 1, case	Cathode
Pin 2	Anode



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Maximum Ratings

1 Maximum Ratings

Table 1 Maximum ratings¹

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	650	V
Continuous forward current for $R_{thJC,max}$ $T_C = 129 ^{\circ}C, D=1$	I _F	16	А
Surge non-repetitive forward current, sine halfwave $T_c=25^{\circ}C$, $t_p=10ms$ $T_c=150^{\circ}C$, $t_p=10ms$	I _{F,SM}	63 51	А
Non-repetitive peak forward current $T_c=25^{\circ}C, t_p=10\mu s$	I _{F,max}	637	А
i^2 t value T_C = 25°C, t_p =10ms T_C = 150°C, t_p =10ms	∫i² dt	20 13	A ² s
Diode dv/dt ruggedness V _R =0480V	dv/dt	100	V/ns
Power dissipation T _C = 25°C	P _{tot}	79	W
Operating temperature	T _j	-40175	°C
Storage temperature	T _{stg}	-55150	°C
ESD			
Human body model, R= 1.5 k Ω , C = 100 pF		8	kV
Charged device model		2	



Thermal Characteristics

2 Thermal Characteristics

Table 2 Thermal Characteristics¹

Darameter	Symbol	Values			Unit	Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.		Note/Test condition
Thermal resistance, junction–case ²	R_{thJC}	-	1.5	1.9	K/W	
Thermal resistance, junction-ambient ²	R_{thJA}	-	-	62	K/W	



Electrical Characteristics

3 Electrical Characteristics

Table 3 Static Characteristics

Parameter	Symbol	Values			Unit	Note/Test condition
Parameter		Min.	Тур.	Max.	Onic	Note/ rest condition
DC blocking voltage	V_{DC}	650	-	-		$T_j = 25$ °C, $I_R = 0.09$ mA
Diode forward voltage ³	V _F	-	1.5	1.7	ŀ	T _j = 25°C, I _F = 16 A
		-	1.8	2.1		$T_j = 150$ °C, $I_F = 16$ A
Reverse current	I _R	-	3	90	μΑ	V _R = 650 V, T _j = 25 °C
		-	19	-		V _R = 650 V, T _j = 150 °C

Table 4 Dynamic Characteristics at Tj=25°C unless noted otherwise

Parameter	Cymhal	Values			Unit	Note/Test condition
Parameter	Symbol Min. Typ. M		Max.	Unit		
Total capacitive charge	Q_{c}	-	23	-	nC	$V_R = 400 \text{ V}, \text{ di/dt} = 200 \text{ A/}\mu\text{s},$ $I_F \le I_{F,MAX}, T_j = 150 \text{ °C}$
Total capacitance	С	-	483	-	pF	V _R = 1 V, f = 1 MHz
		-	57	-		V _R = 300 V, f = 1 MHz
		-	53	-		V _R = 600 V, f = 1 MHz

Footnotes:

¹ The parameter is not subject to production test- verified by design/characterization.

² Rth,JC defined as per JESD-51-14. Rth,JA defined as per JESD-51-5/7.

³ Only the value at 25°C is subject to production test. The value at 150°C is only verified by design/characterization.



Electrical Characteristics Diagrams

4 Electrical Characteristics Diagrams

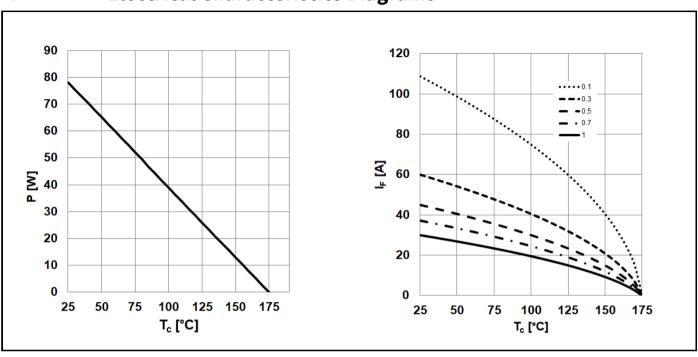


Figure 1 (LEFT) Power dissipation; $P_{tot} = f(T_c)$; $R_{thJC,max}$ (RIGHT) Diode forward current; $I_F = f(T_c)$; $T_i \le 175$ °C; $R_{thJC,max}$; parameter: D=duty cycle

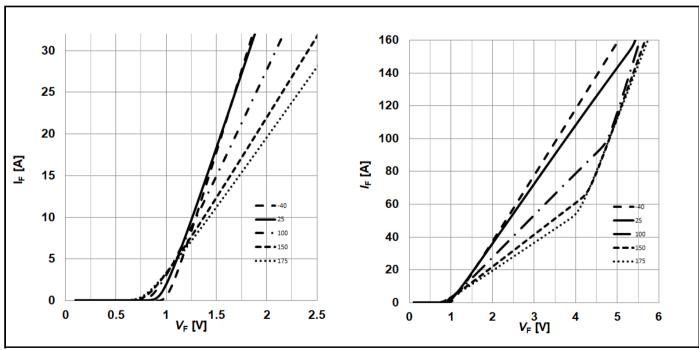


Figure 2 (LEFT) Typical forward characteristic; $I_F = f(V_F)$; $t_P = 20 \mu s$; parameter: T_j (RIGHT) Typical forward characteristics in surge current; $I_F = f(V_F)$; $t_P = 20 \mu s$; parameter: T_j



Electrical Characteristics Diagrams

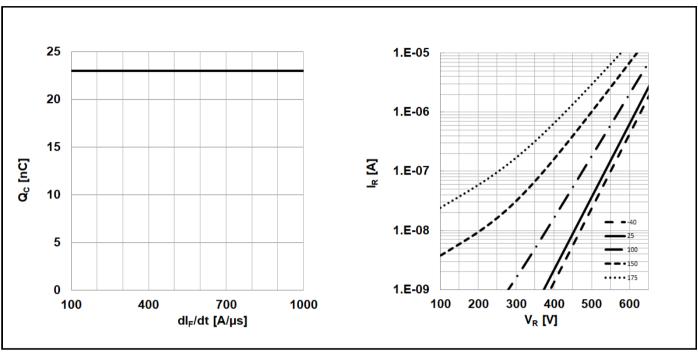


Figure 3 (LEFT) Typical capacitive charge versus current slope (only capacitive charge, guaranteed by design); $Q_C = f(di_F/dt)$; $T_j = 150^{\circ}C$; $V_R = 400V$; $I_F \le I_{F,max}$ (RIGHT) Typical reverse current versus reverse voltage; $I_R = f(V_R)$; parameter: T_i

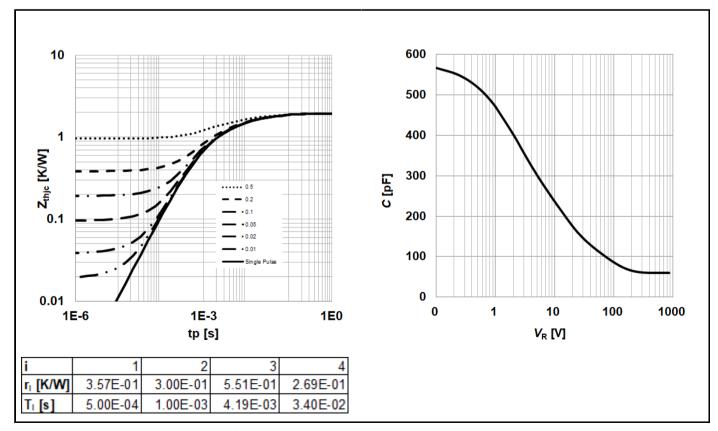


Figure 4 (LEFT) Max. Transient thermal impedance; $Z_{thJC} = f(t_p)$; parameter: $D = t_p/T$ (RIGHT) Typ. Capacitance vs. Reverse voltage; $C = f(V_p)$; $T_i = 25^{\circ}C$; f = 1 MHz



Electrical Characteristics Diagrams

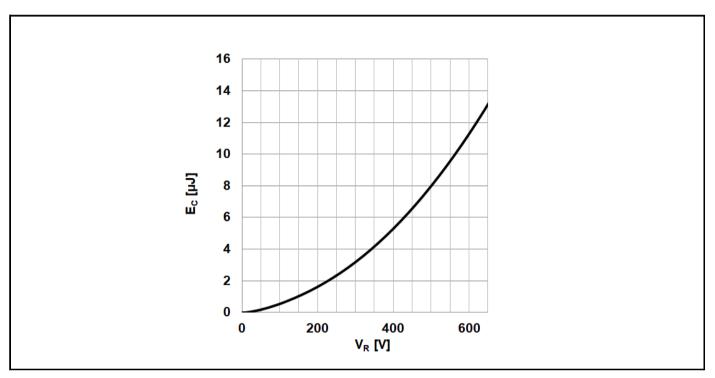


Figure 5 Typical capacitance stored energy; $E_c = f(V_R)$

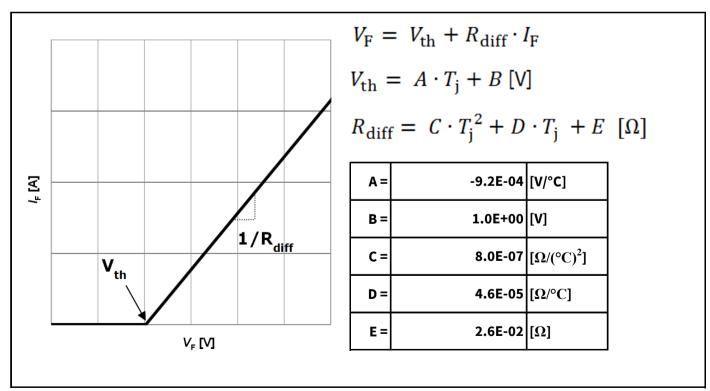


Figure 6 Simplified forward characteristics model $V_F = f(I_F)$; -40°C < T_i <175°C; I_F < 32 A



Package Outlines

5 Package Outlines

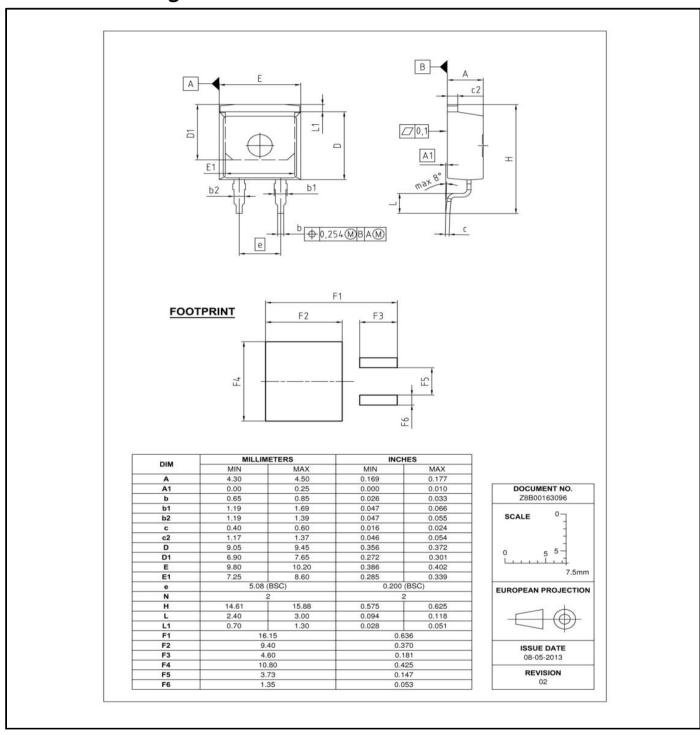


Figure 6 Package outline of PG-TO263-2-1 leaded



Revision History

Revision History

Document Version	Date of Release	Description of changes
V3.0	21.07.2021	1st release of Data Sheet



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